

IN THE CLAIMS

For the convenience of the Examiner, all pending claims of the present Application are shown below in numerical order whether or not an amendment has been made and applying the revised amendment practice of 37 CFR 1.121 – IFW
5 Final Rule.

1. **(Canceled)** An extrusion, comprising:
a plurality of elongate P-type regions extending approximately from a first end
of the extrusion to a second end of the extrusion; and
10 a plurality of elongate N-type regions generally interspersed between and
adjacent to the P-type regions, each N-type region extending approximately from the
first end to the second end.
2. **(Original)** A thermoelectric device, comprising:
15 a P/N-type wafer having a plurality of P-type regions and a plurality of N-type
regions generally interspersed between and adjacent the P-type regions;
a patterned metalization coupled with at least a subset of the P-type regions
and N-type regions; and
first and second plates coupled with the P/N-type wafer.
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3. **(Currently Amended)** The thermoelectric device of Claim 2, wherein
the subset of the P-type regions and N-type regions ~~are~~ is arranged electrically in
series and thermally in parallel.
- 25 4. **(New)** The thermoelectric device of Claim 2, wherein:
the plurality of P-type regions comprises a first number of regions;
the plurality of N-type regions comprises a second number of regions; and
the first number of regions is greater than the second number of regions.

5. **(New)** The thermoelectric device of Claim 2, wherein:
the plurality of P-type regions comprises a first number of regions;
the plurality of N-type regions comprises a second number of regions; and
the first number of regions is equal to the second number of regions.

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6. **(New)** The thermoelectric device of Claim 2, wherein:
the plurality of P-type regions comprises a first number of regions;
the plurality of N-type regions comprises a second number of regions; and
the first number of regions is less than the second number of regions.

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7. **(New)** The thermoelectric device of Claim 2, wherein each of the P-
type regions comprise[[s]] a first generally circular cross-section, and each of the N-
type regions comprise a second generally circular cross-section.

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8. **(New)** The thermoelectric device of Claim 2, wherein each of the P-
type regions comprise a first generally rectangular cross-section, and each of the N-
type regions comprise a second generally rectangular cross-section.

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9. **(New)** The thermoelectric device of Claim 2, further comprising a
passivating agent disposed upon a surface of at least one of the P-type regions and at
least one of the N-type regions.

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10. **(New)** The thermoelectric device of Claim 9, wherein the passivating
agent comprises boron nitride.

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11. **(New)** The thermoelectric device of Claim 2, wherein the P/N-type
wafer and the patterned metallization cooperate to form at least a portion of a
thermoelectric circuit that includes individual legs arranged electrically in series and
thermally in parallel.